

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A full depletion SOI-MOS transistor comprising:

- a substrate having a main surface;
- a buried oxide layer formed on the main surface of the substrate;
- a thin silicon layer ~~formed~~ on the buried oxide layer, the thin silicon layer including a channel region and an impurity diffused ~~[[a]]~~ source/drain region;
- an isolation layer formed on the buried oxide layer, the isolation layer adjacent the thin silicon layer;
- a gate insulation layer formed on the channel region of the thin silicon layer;
- a gate electrode formed on the gate insulation layer; and
- a deposited polysilicon layer ~~formed~~ on the impurity diffused source/drain region of the thin silicon layer, wherein the impurity diffused source/drain region and the deposited polysilicon layer together constitute a source/drain of the full depletion SOI-MOS transistor.

Claim 2 (Previously Presented): A full depletion SOI-MOS transistor according to claim

1, further comprising a sidewall formed on the gate insulation layer, adjacent the gate electrode.

Claim 3 (Currently Amended): A full depletion SOI-MOS transistor according to claim 1, wherein the deposited polysilicon layer extends on the isolation layer.

Claim 4 (Currently Amended): A full depletion SOI-MOS transistor according to claim 2, wherein the deposited polysilicon layer extends on the sidewall.

Claim 5 (Currently Amended): A full depletion SOI-MOS transistor according to claim 1, wherein a thickness of the thin silicon layer is about 20 to 80 percent of a total thickness of the thin silicon layer and the deposited polysilicon layer.

Claim 6 (Previously Presented): A full depletion SOI-MOS transistor according to claim 1, wherein a thickness of the thin silicon layer is less than about 35 nm.

Claims 7-12 (Canceled)

Claim 13 (Currently Amended): A full depletion SOI-MOS transistor comprising:

a substrate having a main surface;

a BOX layer formed on the main surface of the substrate;

an SOI layer ~~formed~~ on the BOX layer, the SOI layer including a channel region and ~~[[a]]~~ an impurity diffused source/drain region;

an isolation layer formed on the BOX layer, the isolation layer adjacent the SOI layer;

a gate insulation layer formed on the channel region of the SOI layer;

a gate electrode formed on the gate insulation layer; and

a deposited high mobility conductive layer ~~formed~~ on the impurity diffused source/drain region of the thin silicon layer, wherein the deposited high mobility conductive layer ~~containing~~ contains polysilicon and wherein the impurity diffused source/drain region and the deposited high mobility conductive layer together constitute a source/drain of the full depletion SOI-MOS transistor.

Claim 14 (Previously Presented): A full depletion SOI-MOS transistor according to claim 13, further comprising a sidewall formed on the gate insulation layer, adjacent the gate electrode.

Claim 15 (Currently Amended): A full depletion SOI-MOS transistor according to claim 13, wherein the deposited high mobility conductive layer extends on the isolation layer.

Claim 16 (Currently Amended): A full depletion SOI-MOS transistor according to claim 14, wherein the deposited high mobility conductive layer extends on the sidewall.

Claim 17 (Currently Amended): A full depletion SOI-MOS transistor according to claim 13, wherein a thickness of the SOI layer is about 20 to 80 percent of a total thickness of the SOI layer and the deposited high mobility conductive layer.

Claim 18 (Previously Presented): A full depletion SOI-MOS transistor according to claim 13, wherein a thickness of the SOI layer is less than about 35 nm.

Claim 19 (Currently Amended): A full depletion SOI-MOS transistor according to claim 13, wherein the deposited high mobility conductive layer contains silicide.

Claim 20 (Currently Amended): A full depletion SOI-MOS transistor according to claim 19, wherein the deposited high mobility conductive layer is formed on the gate electrode.